

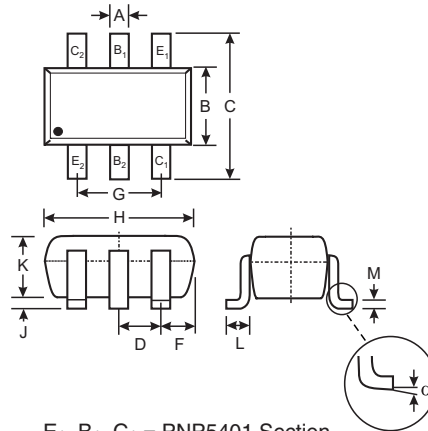
COMPLEMENTARY NPN / PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

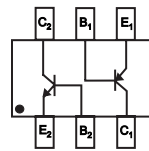
- Complementary Pair
- One 5551-Type NPN,
One 5401-Type PNP
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- **Lead Free/RoHS Compliant (Note 3)**

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking (See Page 3): KNM
- Ordering & Date Code Information: See Page 3
- Weight: 0.006 grams (approx.)



E₁, B₁, C₁ = PNP5401 Section
 E₂, B₂, C₂ = NPN5551 Section



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Maximum Ratings, NPN 5551 Section @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	NPN5551	Unit
Collector-Base Voltage	V _{CBO}	180	V
Collector-Emitter Voltage	V _{CEO}	160	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous (Note 1)	I _C	200	mA
Power Dissipation (Note 1, 2)	P _d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	625	K/W
Operating and Storage and Temperature Range	T _j , T _{STG}	-55 to +150	°C

Maximum Ratings, PNP 5401 Section @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	PNP5401	Unit
Collector-Base Voltage	V _{CBO}	-160	V
Collector-Emitter Voltage	V _{CEO}	-150	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current - Continuous (Note 1)	I _C	-200	mA
Power Dissipation (Note 1, 2)	P _d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	625	K/W
Operating and Storage and Temperature Range	T _j , T _{STG}	-55 to +150	°C

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. Maximum combined dissipation.
 3. No purposefully added lead.

Electrical Characteristics, NPN 5551 Section

@ T_A = 25°C unless otherwise specified

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Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	180	—	V	I _C = 100μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	160	—	V	I _C = 1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0	—	V	I _E = 10μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	50	nA μA	V _{CB} = 120V, I _E = 0 V _{CB} = 120V, I _E = 0, T _A = 100°C
Emitter Cutoff Current	I _{EBO}	—	50	nA	V _{EB} = 4.0V, I _C = 0
ON CHARACTERISTICS (Note 4)					
DC Current Gain	h _{FE}	80 80 30	— 250 —	—	I _C = 1.0mA, V _{CE} = 5.0V I _C = 10mA, V _{CE} = 5.0V I _C = 50mA, V _{CE} = 5.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	0.15 0.20	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	1.0	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	6.0	pF	V _{CB} = 10V, f = 1.0MHz, I _E = 0
Small Signal Current Gain	h _{fe}	50	250	—	V _{CE} = 10V, I _C = 1.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f _T	100	300	MHz	V _{CE} = 10V, I _C = 10mA, f = 100MHz
Noise Figure	NF	—	8.0	dB	V _{CE} = 5.0V, I _C = 200μA, R _S = 1.0kΩ, f = 1.0kHz

Electrical Characteristics, PNP 5401 Section

@ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-160	—	V	I _C = -100μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-150	—	V	I _C = -1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0	—	V	I _E = -10μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	-50	nA μA	V _{CB} = -120V, I _E = 0 V _{CB} = -120V, I _E = 0, T _A = 100°C
Emitter Cutoff Current	I _{EBO}	—	-50	nA	V _{EB} = -3.0V, I _C = 0
ON CHARACTERISTICS (Note 4)					
DC Current Gain	h _{FE}	50 60 50	— 240 —	—	I _C = -1.0mA, V _{CE} = -5.0V I _C = -10mA, V _{CE} = -5.0V I _C = -50mA, V _{CE} = -5.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	-0.2 -0.5	V	I _C = -10mA, I _B = -1.0mA I _C = -50mA, I _B = -5.0mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	-1.0	V	I _C = -10mA, I _B = -1.0mA I _C = -50mA, I _B = -5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	6.0	pF	V _{CB} = -10V, f = 1.0MHz, I _E = 0
Small Signal Current Gain	h _{fe}	40	200	—	V _{CE} = -10V, I _C = -1.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f _T	100	300	MHz	V _{CE} = -10V, I _C = -10mA, f = 100MHz
Noise Figure	NF	—	8.0	dB	V _{CE} = -5.0V, I _C = -200μA, R _S = 10Ω, f = 1.0kHz

Notes: 4. Short duration test pulse used to minimize self-heating effect.

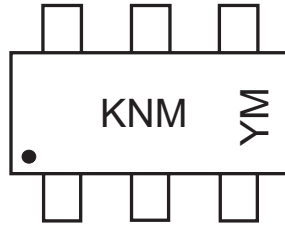
Ordering Information (Note 5)

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Device	Packaging	Shipping
MMDT5451-7-F	SOT-363	3000/Tape & Reel

Notes: 5. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information

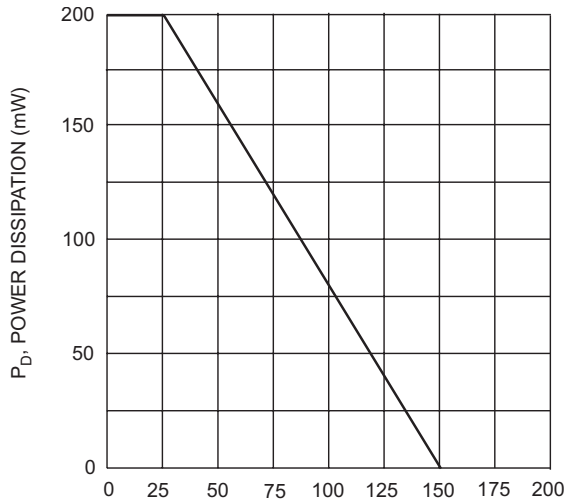


KNM= Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: N = 2002
 M = Month ex: 9 = September

Date Code Key

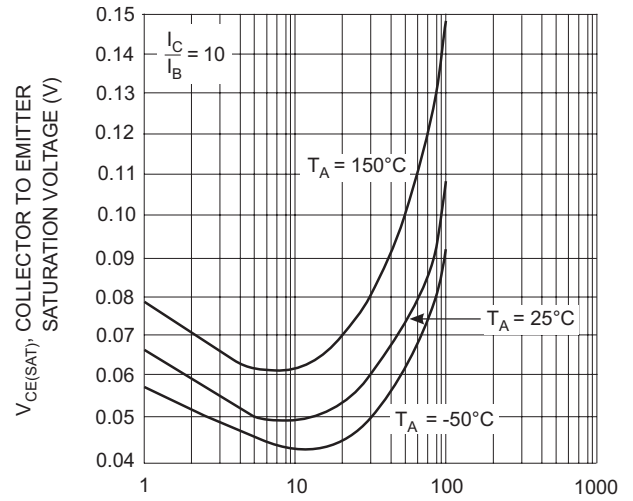
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



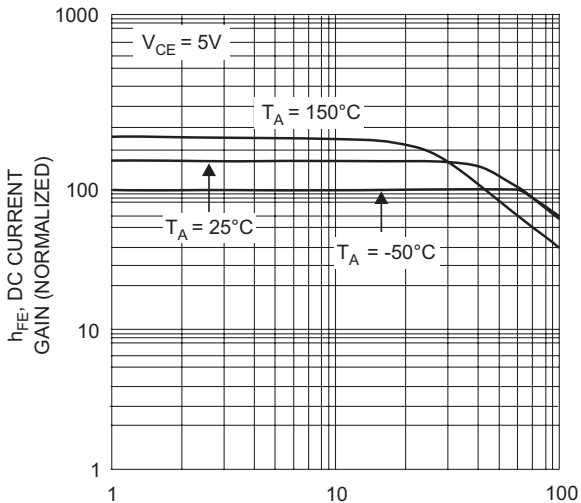
T_A , AMBIENT TEMPERATURE (°C)

Fig. 1, Max Power Dissipation vs Ambient Temperature (Total Device)



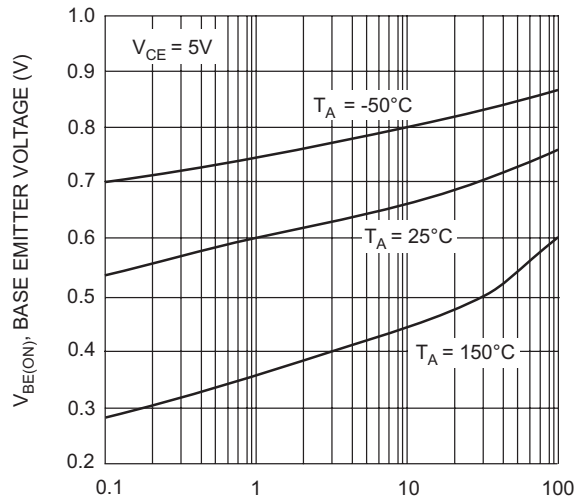
I_C , COLLECTOR CURRENT (mA)

Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current (NPN5551)



I_C , COLLECTOR CURRENT (mA)

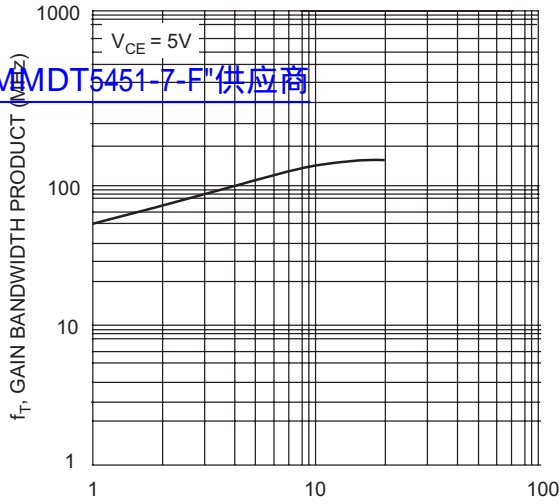
Fig. 3, DC Current Gain vs Collector Current (NPN5551)



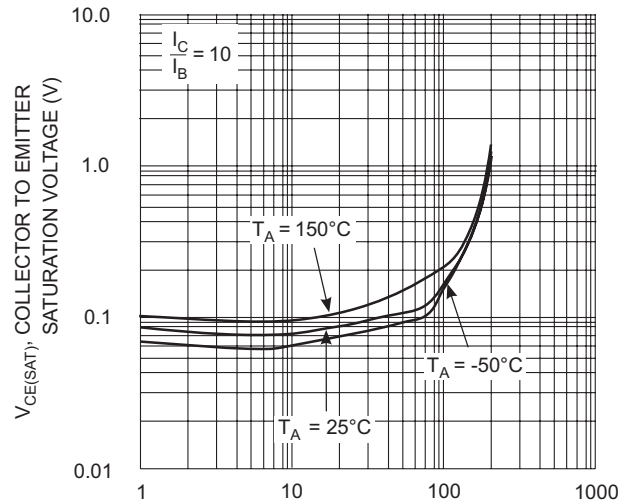
I_C , COLLECTOR CURRENT (mA)

Fig. 4, Base Emitter Voltage vs. Collector Current (NPN5551)

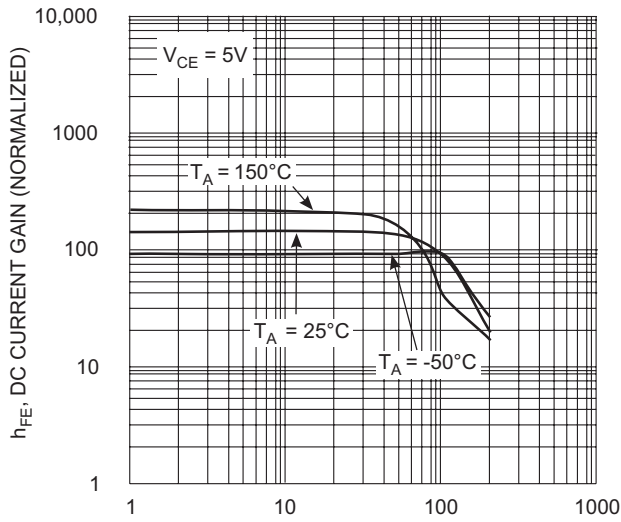
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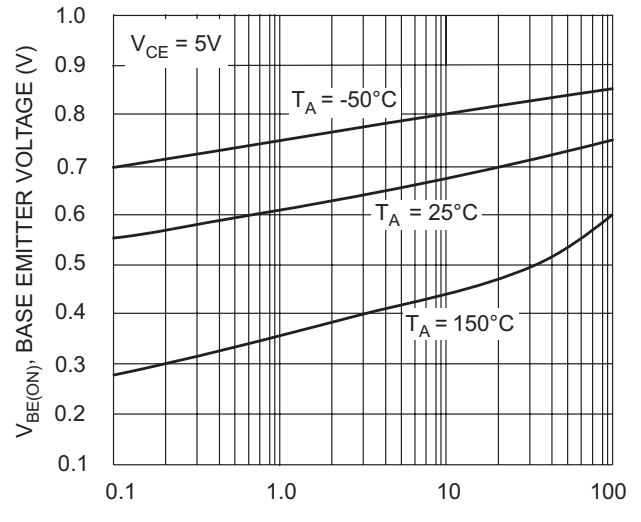
I_C , COLLECTOR CURRENT (mA)
Fig. 5. Gain Bandwidth Product vs. Collector Current (NPN5551)



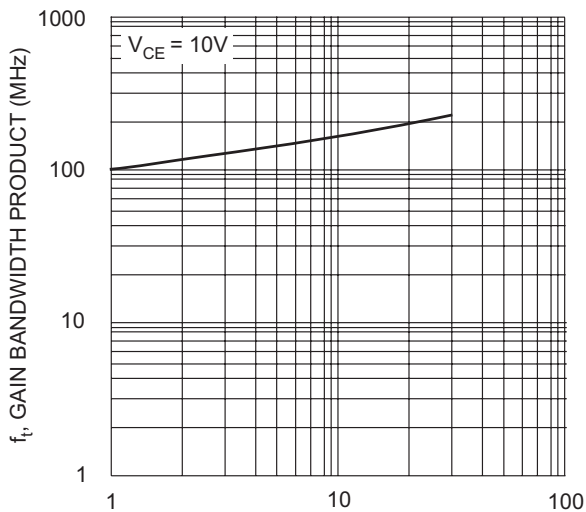
I_C , COLLECTOR CURRENT (mA)
Fig. 6. Collector Emitter Saturation Voltage vs. Collector Current (PNP5401)



I_C , COLLECTOR CURRENT (mA)
Fig. 7. DC Current Gain vs. Collector Current (PNP5401)



I_C , COLLECTOR CURRENT (mA)
Fig. 8. Base Emitter Voltage vs. Collector Current (PNP5401)



I_C , COLLECTOR CURRENT (mA)
Fig. 9. Gain Bandwidth Product vs Collector Current (PNP5401)

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